

SLAC ILC Damping Ring Kicker High Availability Modulator R&D Program

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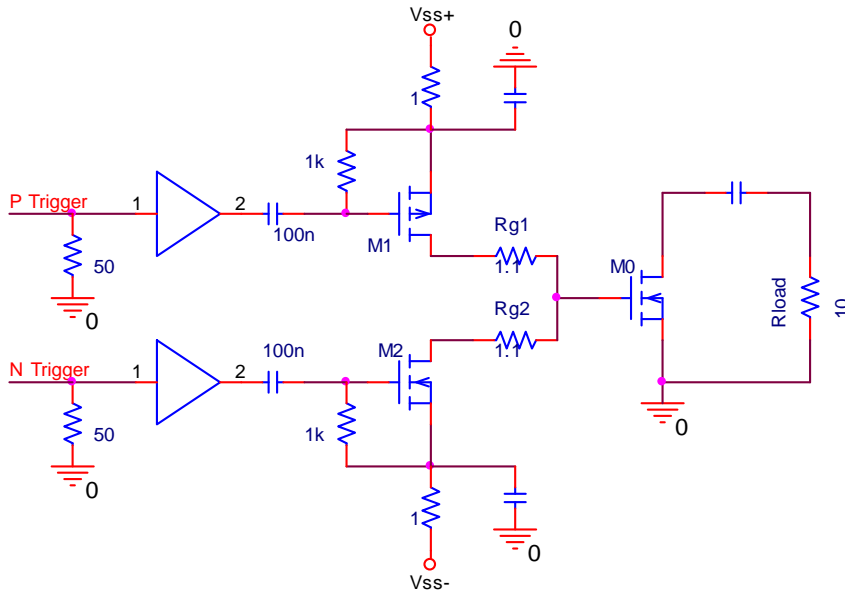
A. Krasnykh, R. Larsen, T. Tang (SLAC)
E. Cook (LLNL)

Overview

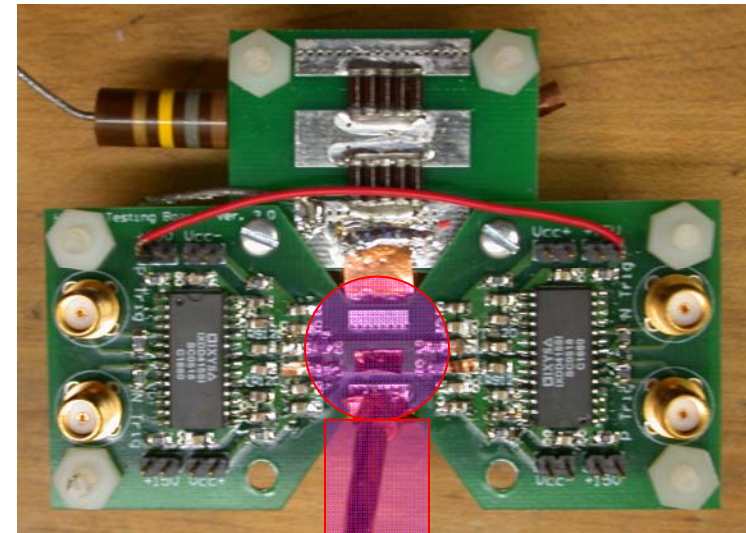
- SLAC program is investigating two approaches
 - MOSFET array (adder) topologies
 - DSRD (opening switch) topologies
- FY09 Program structure
- FY08 MOSFET array results
- FY08 DSRD (Krasnykh next talk)
 - Diagnostic development
 - MOSFET-based “pump”

- MOSFET Array
 - Sub-system/Scale modulator
 - ¼ FTE
 - DOE-ILC funding, subject to CR
- DSRD
 - ATF2 kicker modulator
 - ± 5 kV, 50Ω , $T_{\text{flattop}} \sim 2$ ns, $T_r/T_f \sim 1$ ns, 6 MHz
 - Developmental DSRD (T_{burst} thermally limited)
 - Deliver prototype to KEK end CY10
 - ¼ FTE
 - US-Japan funding

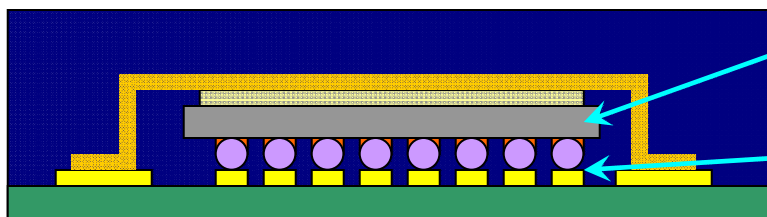
MOSFET/Driver Hybrid



Circuit diagram



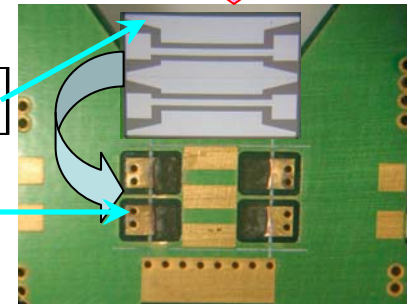
FET mounted on back side of PCB



Flip-Chip assembly

MOSFET Die

Pads

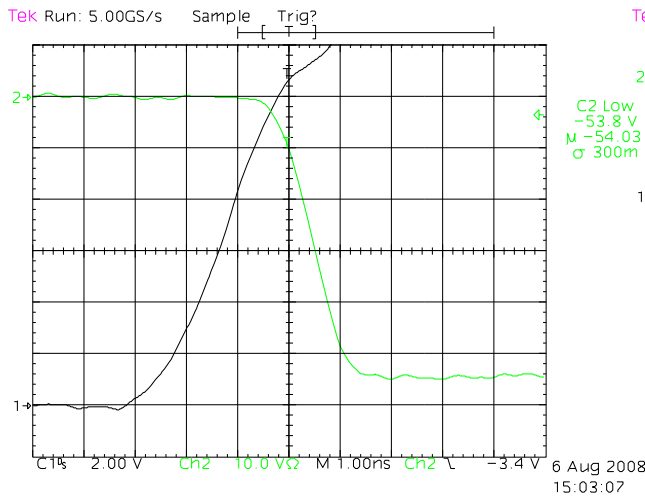


1200 V, 48 A MOSFET Hybrid Prototype Results

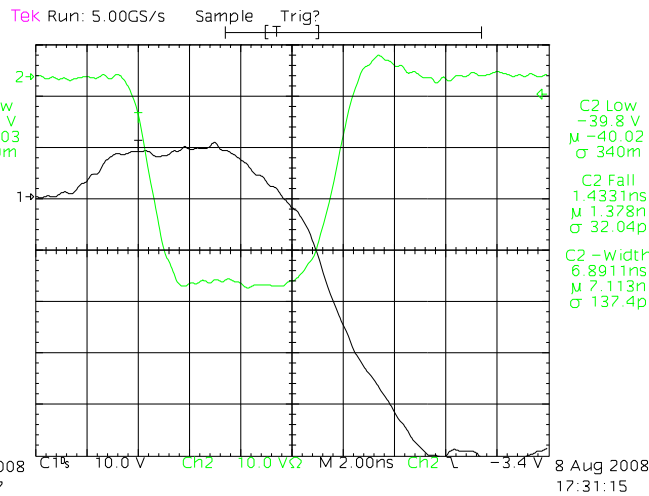
Fastest switching speed: 1.2 ns

Shortest pulse width (FWHM): 7.1 ns

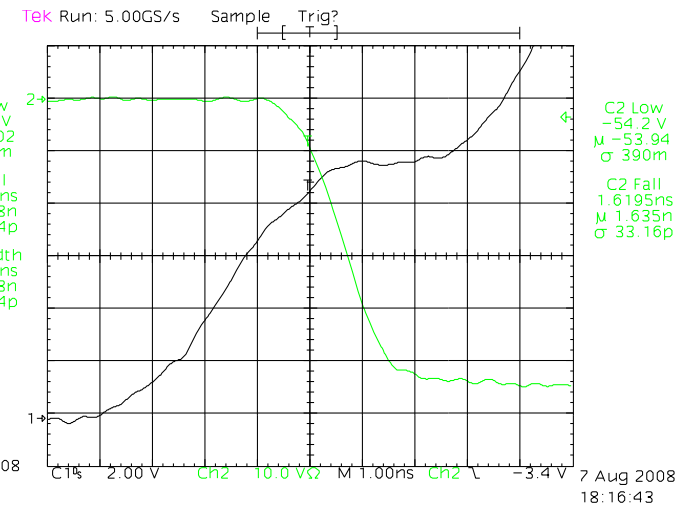
Excellent gate control



$V_{DS}=1\text{kV}$, $R_{Load}=27\text{ ohm}$, $I_D=33\text{ A}$

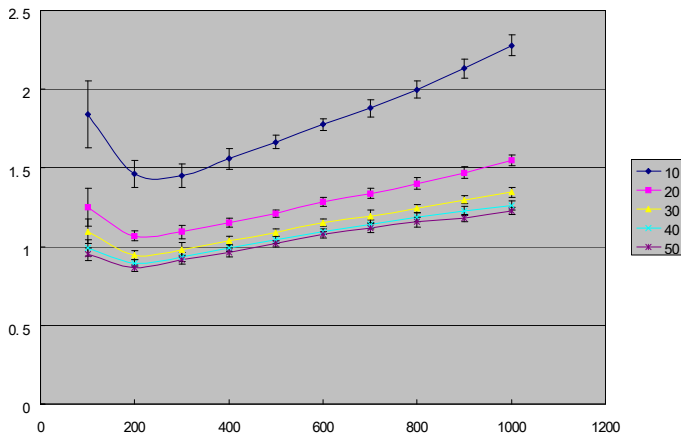


$V_{DS}=1\text{kV}$, $R_{Load}=10\text{ ohm}$, $I_D=68\text{ A}$



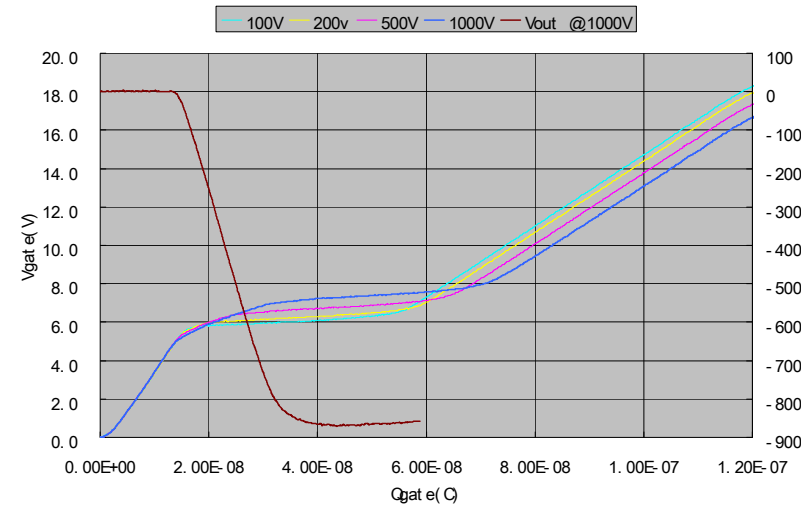
$V_{DS}=1\text{kV}$, $R_{Load}=27\text{ ohm}$, $I_D=33\text{ A}$

Switching Speed



MOSFET switching speed dependence on driver voltage (current) and MOSFET charge voltage (load current)

Switching Characteristics



MOSFET gate voltage and switching dependence on gate charge

- Transmission line adder
 - 4-stage demonstration
 - Verify hybrid risetime can be preserved through adder structure
- Advanced hybrid development
 - Optimize driver for short (<5 ns) output pulse
 - Improve hybrid construction
 - Select optimum MOSFET (voltage, current, speed)
- “Scale” modulators
 - Parallel arrays of hybrids for low Z modules
 - Bi-polar adder

Summary

- FY08 Results
 - Modest progress (funding limitations)
 - Ultra-fast switching: hybrid circuit achieves fundamental MOSFET limit w/ excellent control
 - High bandwidth HV diagnostics (Krasnykh)
 - DSRD “pump” development (Krasnykh)
- FY09 Program
 - “Scaled” inductive adder assemblies
 - Prototype DSRD modulator for ATF2